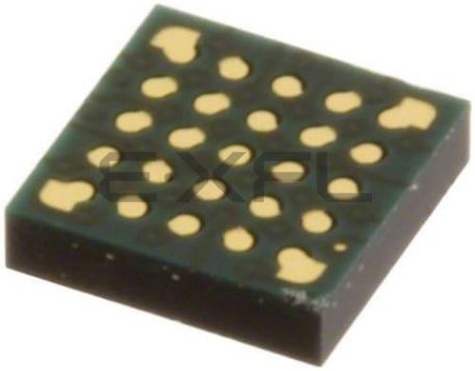

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, WDT
Number of I/O	21
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 11x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	25-WFLGA
Supplier Device Package	25-LGA (3x3)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1058agla-w0

Pin count	Package	Ordering Part Number
10 pins	10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65 mm pitch)	R5F1051AGSP#30, R5F1051AASP#30 R5F1051AGSP#50, R5F1051AASP#50
16 pins	16-pin plastic SSOP (4.4 × 5.0 mm, 0.65 mm pitch)	R5F1054AGSP#30, R5F1054AASP#30 R5F1054AGSP#50, R5F1054AASP#50
20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	R5F1056AGSP#30,R5F1056AASP#30 R5F1056AGSP#50,R5F1056AASP#50
24 pins	24-pin plastic HWQFN (4 × 4 mm, 0.50 mm pitch)	R5F1057AGNA#U0,R5F1057AANA#U0 R5F1057AGNA#W0,R5F1057AANA#W0
25 pins	25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)	R5F1058AGLA#U0,R5F1058AALA#U0 R5F1058AGLA#W0,R5F1058AALA#W0

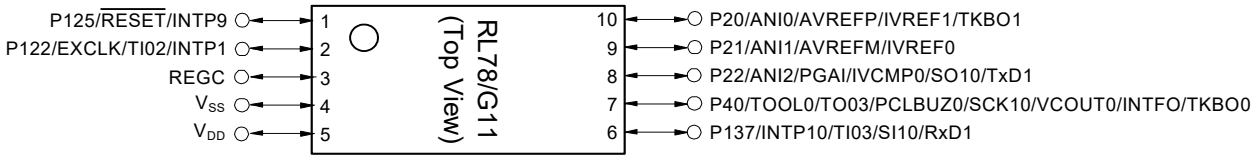
Caution 1. For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11.

Caution 2. The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

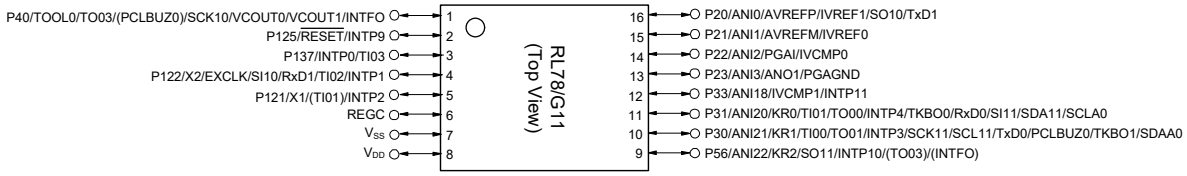
1.3.1 10-pin products

• 10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65 mm pitch)



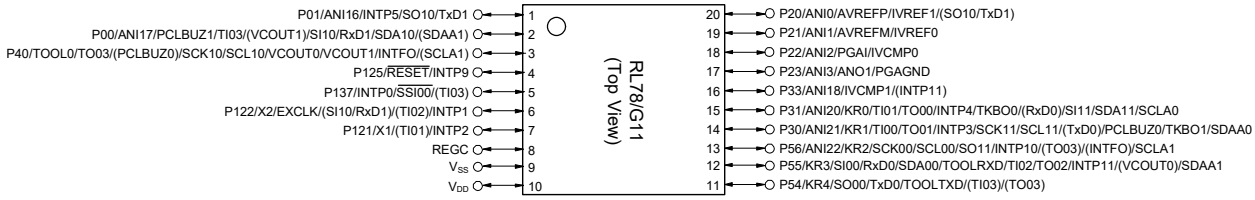
1.3.2 16-pin products

• 16-pin plastic SSOP (4.4 × 5.0 mm, 0.65 mm pitch)



1.3.3 20-pin products

• 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				20.0 Note 2	mA
		Total of P00, P01, and P40 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD} ≤ 5.5 V			70.0	mA
			2.7 V ≤ EV_{DD} < 4.0 V			15.0	mA
			1.8 V ≤ EV_{DD} < 2.7 V			9.0	mA
			1.6 V ≤ EV_{DD} < 1.8 V			4.5	mA
		Total of P30 to P33, and P51 to P56 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD} ≤ 5.5 V			80.0	mA
			2.7 V ≤ EV_{DD} < 4.0 V			35.0	mA
			1.8 V ≤ EV_{DD} < 2.7 V			20.0	mA
			1.6 V ≤ EV_{DD} < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	I_{OL2}	Per pin for P20 to P23				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 5.5 V			1.6	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA
Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≈ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(3/5)**

<R>

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0.8 EV_{DD}		EV_{DD}	V
	V_{IH2}	P00, P30 to P32, P40, P51 to P56	TTL mode 4.0 V ≤ EV_{DD} ≤ 5.5 V	2.2		EV_{DD}	V
			TTL mode 3.3 V ≤ EV_{DD} < 4.0 V	2.0		EV_{DD}	V
			TTL mode 1.6 V ≤ EV_{DD} < 3.3 V	1.5		EV_{DD}	V
	V_{IH3}	P20 to P23 (digital input)		0.7 V_{DD}		V_{DD}	V
	V_{IH4}	P121, P122, P125, P137, EXCLK, $\overline{RESET}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0		0.2 EV_{DD}	V
	V_{IL2}	P00, P30 to P32, P40, P51 to P56	TTL mode 4.0 V ≤ EV_{DD} ≤ 5.5 V	0		0.8	V
			TTL mode 3.3 V ≤ EV_{DD} < 4.0 V	0		0.5	V
			TTL mode 1.6 V ≤ EV_{DD} < 3.3 V	0		0.32	V
	V_{IH3}	P20 to P23 (digital input)		0		0.3 V_{DD}	V
	V_{IH4}	P121, P122, P125, P137, EXCLK, $\overline{RESET}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00, P01, P20, P30 to P33, P40 and P51 to P56 is V_{DD} or EV_{DD}, even in the N-ch open-drain mode.
(P20: V_{DD}
P00, P01, P30 to P33, P40, P51 to P56: EV_{DD})

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.4 AC Characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V PMMC. MCSEL = 0	0.125		1	μs
				1.8 V ≤ V_{DD} ≤ 5.5 V PMMC. MCSEL = 1	0.25		1	
			LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	1			μs
			LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
		Subsystem clock (f_{SUB}) operation	f_{IL}	1.8 V ≤ V_{DD} ≤ 5.5 V		66.7		μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1		20	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1		16	MHz
		1.8 V ≤ V_{DD} < 2.4 V			1		8	MHz
		1.6 V ≤ V_{DD} < 1.8 V			1		4	MHz
External system clock input high-/low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
		1.8 V ≤ V_{DD} < 2.4 V			60			ns
		1.6 V ≤ V_{DD} < 1.8 V			120			ns
TI00 to TI03 input high-/low-level width	t_{TIH}, t_{TIL} Note				1/f_{MCK} + 10			ns

Note Following conditions must be satisfied on low level interface of EV_{DD} < V_{DD}.
1.8 V ≤ EV_{DD} ≤ 2.7 V: MIN. 125 ns
1.6 V ≤ EV_{DD} < 1.8 V: MIN. 250 ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		Note 1		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note 2		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 3		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 5, 6		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD} ≤ 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 4. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with EV_{DD} ≥ V_b.

(7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		1150		1150		ns
		$t_{KCY1} \geq 2/f_{CLK}$	2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300								ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 7		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 10								
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		479		479		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121								
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		10		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ										
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60		60		60	ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130		130	
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23		110		110		110		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33								
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		10		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ										

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		1150		1150		ns
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500								ns
			1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ	1150								ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 12		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 18								
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 50								ns

Note Use it with $EV_{DD} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EV_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the page after the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel \ Reference Voltage	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-)= AV_{REFM}
ANI0 to ANI3	Refer to **2.6.1 (1)**.	Refer to **2.6.1 (3)**.	Refer to **2.6.1 (4)**.
ANI16 to ANI22	Refer to **2.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **2.6.1 (1)**.		—

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV_{REFP} = V_{DD} Note 3	1.8 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±3.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V Note 4		1.2	±7.0	LSB
Conversion time	tCONV	10-bit resolution Target pin: ANI2 and ANI3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution AV_{REFP} = V_{DD} Note 3	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V Note 4			±0.50	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution AV_{REFP} = V_{DD} Note 3	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V Note 4			±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV_{REFP} = V_{DD} Note 3	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±2.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV_{REFP} = V_{DD} Note 3	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±1.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V Note 4			±2.0	LSB
Analog input voltage	VAIN	ANI2 and ANI3		0		AV_{REFP}	V
		Internal reference voltage (1.8 V ≤ V_{DD} ≤ 5.5 V)		V_{BGR} Note 5			V
		Temperature sensor output voltage (1.8 V ≤ V_{DD} ≤ 5.5 V)		V_{TMPS25} Note 5			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Note 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

Note 5. Refer to **2.6.2 Temperature sensor characteristics/internal reference voltage characteristic**.

2.6.4 Comparator

(Comparator 0: T_A = -40 to +85°C, 2.7 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(Comparator 1: T_A = -40 to +85°C, 1.6 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	V_{IREF0}	IVREF0 pin		0		V_{DD} - 1.4 Note 1	V
	V_{IREF1}	IVREF1 pin		1.4 Note 1		V_{DD}	V
	V_{ICMP}	IVCMP0 pin		-0.3		V_{DD} + 0.3	V
		IVCMP1 pin		-0.3		EV_{DD} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/μs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			1.5	μs
			Comparator low-speed mode, standard mode		3		μs
			Comparator low-speed mode, window mode		4		μs
Operation stabilization wait time	t_{CMP}			100			μs
Reference voltage declination in channel 0 of internal DAC Note 2	⊿VIDAC					± 2.5	LSB

Note 1. In window mode, make sure that V_{REF1} - V_{REF0} ≥ 0.2 V.

Note 2. Only in CMP0

2.6.5 PGA

(T_A = -40 to +85°C, 2.7 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	V_{IOPGA}					±10	mV
Input voltage range	V_{IPGA}			0		0.9 × V_{DD}/Gain	V
Output voltage range	V_{IOHPGA}			0.93 × V_{DD}			V
	V_{IOLPGA}					0.07 × V_{DD}	V
Gain error		x4, x8				±1	%
		x16				±1.5	%
		x32				±2	%
Slew rate	SR_{RPGA}	Rising When V_{IN} = 0.1V_{DD}/gain to 0.9V_{DD}/gain. 10 to 90% of output voltage amplitude	4.0 V ≤ V_{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
			4.0 V ≤ V_{DD} ≤ 5.5 V (x32)	3.0			
			2.7 V ≤ V_{DD} ≤ 4.0V	0.5			
	SR_{FPGA}	Falling When V_{IN}= 0.1V_{DD}/gain to 0.9V_{DD}/gain. 90 to 10% of output voltage amplitude	4.0 V ≤ V_{DD} ≤ 5.5 V (Other than x32)	3.5			
			4.0 V ≤ V_{DD} ≤ 5.5 V (x32)	3.0			
			2.7 V ≤ V_{DD} ≤ 4.0V	0.5			
Reference voltage stabilization wait time[Note]	t_{PGA}	x4, x8				5	µs
		x16, x32				10	µs

Note Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

3. ELECTRICAL SPECIFICATIONS (T_A = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications (T_A = −40 to +105°C)

R5F105xxGxx

Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G11 User's Manual.

Caution 3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Caution 4. When operating temperature exceeds 85°C, only HS (high-speed main) mode can be used as the flash operation mode. Regulator mode should be used with the normal setting (MCSEL = 0).

Caution 5. The EV_{DD} pin is not present on products with 24 or less pins. Accordingly, replace EV_{DD} with V_{DD} and the voltage condition $1.6 \leq EV_{DD} \leq V_{DD} \leq 5.5$ V with $1.6 \leq V_{DD} \leq 5.5$ V.

Remark When the products “G: Industrial applications" is used in the range of T_A = -40 to +85°C, see **2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

Fields of application	A: Consumer applications	G: Industrial applications
Operating ambient temperature	T_A = −40 to +85°C	T_A = −40 to +105°C
Operating mode Operating Voltage Range	HS (High-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 24 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 16 MHz LS (Low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 8 MHz LV (Low-voltage main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 4 MHz	Only in HS (High-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 24 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 16 MHz
High-speed on-chip oscillator clock to an accuracy	1.8 V ≤ V_{DD} ≤ 5.5 V: ±1.0% @ T_A = -20 to +85°C ±1.5% @ T_A = -40 to -20°C 1.6 V ≤ V_{DD} < 1.8 V: ±5.0% @ T_A = -20 to +85°C ±5.5% @ T_A = -40 to -20°C	2.4 V ≤ V_{DD} ≤ 5.5 V: ±2.0% @ T_A = +85 to +105°C ±1.0% @ T_A = -20 to +85°C ±1.5% @ T_A = -40 to -20°C
Serial array unit	UART CSI: f_{CLK}/2 (12 Mbps are supported), f_{CLK}/4 Simplified I^2C	UART CSI: f_{CLK}/4 Simplified I^2C
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fast mode
Voltage Detector	• Rising: 1.67 V to 4.06 V (14 levels) • Falling: 1.63 V to 3.98 V (14 levels)	• Rising: 2.61 V to 4.06 V (8 levels) • Falling: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics for "G: Industrial applications" differ from those for "A: Consumer applications" when the product is in use in an ambient temperature over 85°C. For details, see **3.1** to **3.10** in the following pages.

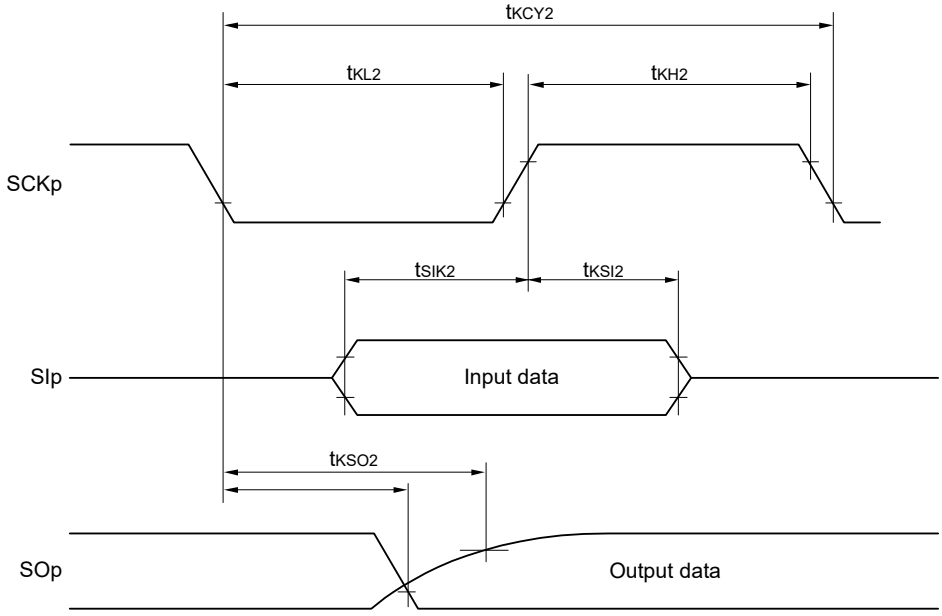
(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
$\overline{SSI00}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	240		ns
			2.4 V ≤ V_{DD} < 2.7 V	400		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	1/f_{MCK} + 240		ns
			2.4 V ≤ V_{DD} < 2.7 V	1/f_{MCK} + 400		ns
$\overline{SSI00}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	1/f_{MCK} + 240		ns
			2.4 V ≤ V_{DD} < 2.7 V	1/f_{MCK} + 400		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	240		ns
			2.4 V ≤ V_{DD} < 2.7 V	400		ns

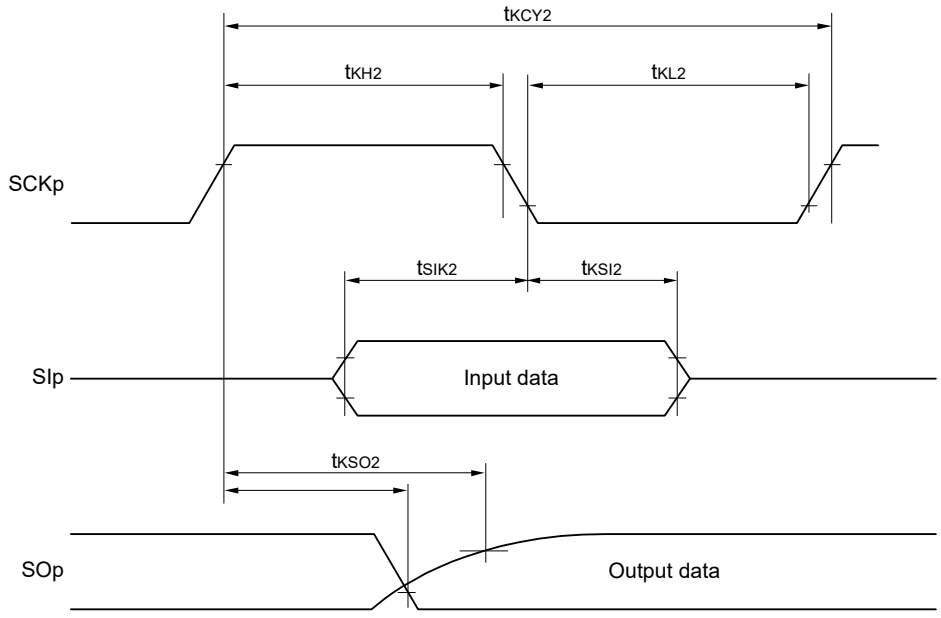
Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5, 12)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



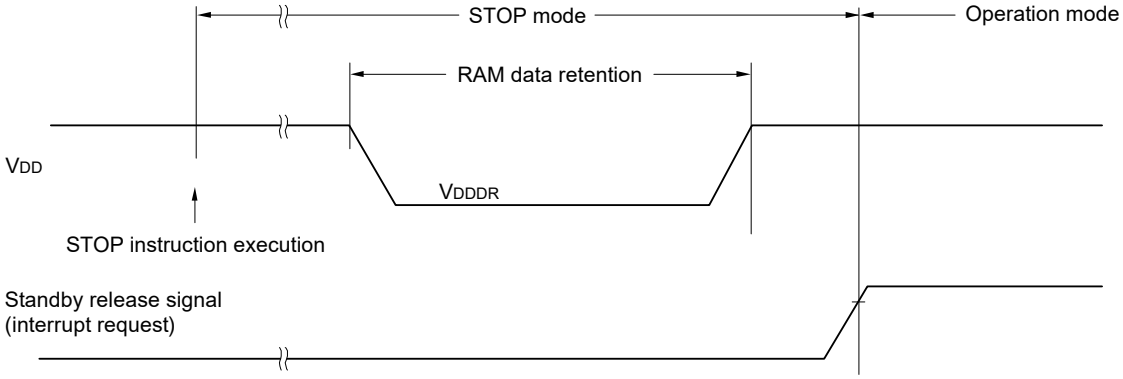
Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

3.7 RAM Data Retention Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}			1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years	T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year	T_A = 25°C		1,000,000		
		Retained for 5 years	T_A = 85°C	100,000			
		Retained for 20 years	T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

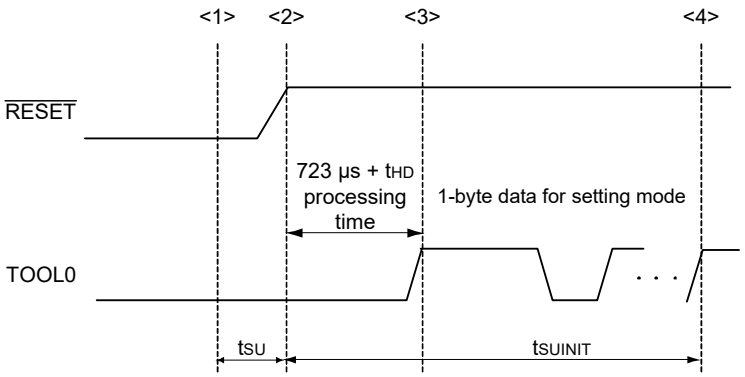
(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified Note 1	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) Notes 1, 2	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μs).

<R>



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

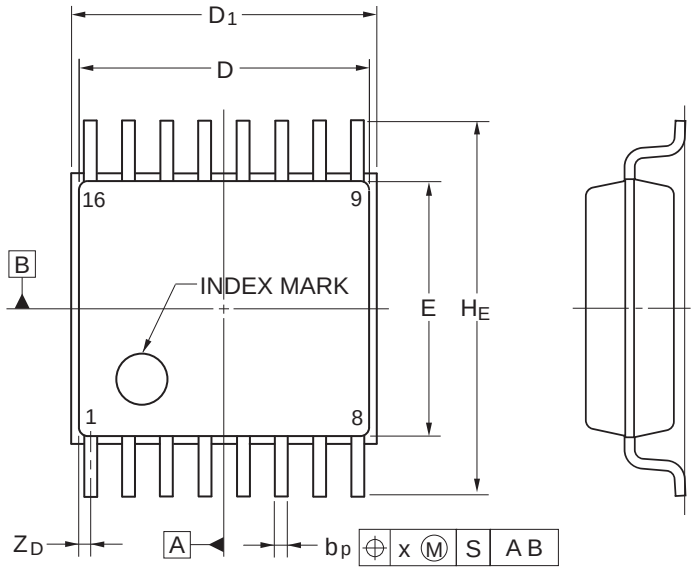
t_{SU}: How long from when the TOOL0 pin is placed at the low level until a pin reset ends

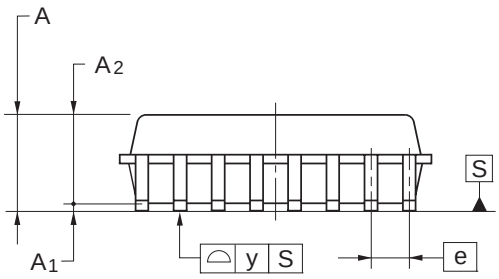
t_{HD}: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

4.2 16-pin products

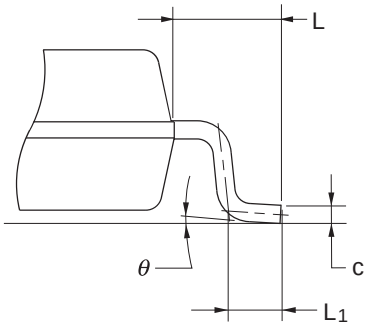
R5F1054AGSP, R5F1054AASP

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-SSOP16-4.4x5-0.65	PRSP0016JC-B	P16MA-65-FAB	0.08



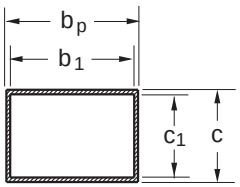


detail of lead end



Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	4.85	5.00	5.15
D_1	5.05	5.20	5.35
E	4.20	4.40	4.60
A_2	—	1.50	—
A_1	0.075	0.125	0.175
A	—	—	1.725
b_p	0.17	0.24	0.32
b_1	—	0.22	—
c	0.14	0.17	0.20
c_1	—	0.15	—
θ	0°	—	8°
H_E	6.20	6.40	6.60
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
Z_D	—	0.225	—
L	0.35	0.50	0.65
L_1	—	1.00	—

Terminal cross section



REVISION HISTORY	RL78/G11 Datasheet

Rev.	Date	Description	
		Page	Summary
0.50	Mar 31 2016	—	First Edition issued
1.00	Sep 28 2016	p.7	Modification of Pin Configuration in 1.3.3 25-pin products
		p.9	Addition of 1.5.1 20-pin products
		p.10	Addition of product name and Modification of Block Diagram in 1.5.2 24-pin, 25-pin products
		p.12	Addition of I^2C bus in 1.6 Outline of Functions
		p.15	Modification of Conditions of I_{OH1}, I_{OL1} in 2.1 Absolute Maximum Ratings
		p.16	Modification of High-speed on-chip oscillator clock frequency accuracy and addition of D_{IMT}, D_{IMV} in 2.2.2 On-chip oscillator characteristics
		p.17	Modification of Caution in 2.3.1 Pin characteristics
		p.19	Modification of Input voltage, high and Input voltage, low in 2.3.1 Pin characteristics
		p.19, 20	Modification of Caution in 2.3.1 Pin characteristics
		p.22, 23, 24, 26, 27	Modification of specifications in 2.3.2 Supply current characteristics
		p.29, 30	Modification of specification in 2.4 AC Characteristics
		p.35	Modification of specifications in 2.5.1 Serial array unit (1)
		p.39	Modification of specifications in 2.5.1 Serial array unit (3)
		p.40, 42	Modification of specification in 2.5.1 Serial array unit (4)
		p.62	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (1)
		p.64	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (2)
		p.65	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (3)
		p.70	Modification of Conditions in 2.6.2 Temperature sensor haracteristics/internal reference voltage characteristic
		p.79	Addition of description in 3 ELECTRICAL SPECIFICATIONS (TA = -40 to +105°C)
		p.82	Modification of High-speed on-chip oscillator clock frequency accuracy and addition of D_{IMT}, D_{IMV} in 3.2.2 On-chip oscillator characteristics
		p.83	Modification of Caution in 3.3.1 Pin characteristics
		p.85	Modification of Input voltage, high and Input voltage, low in 3.3.1 Pin characteristics
		p.85, 86	Modification of Caution in 3.3.1 Pin characteristics
		p.88 to 91	Modification of specifications in 3.3.2 Supply current characteristics
		p.97	Modification of specifications and specification table in 3.5.1 Serial array unit (1)
		p.103	Modification of specifications in 3.5.1 Serial array unit (3)
		p.125	Modification of Conditions in 3.6.1 A/D converter characteristics (4)
		p.126	Modification of Conditions in 3.6.2 Temperature sensor haracteristics/internal reference voltage characteristic
1.10	Dec 28 2016	p.4	Modification of 1.2 Ordering Information
2.00	Feb 15, 2018	Throughout	Addition of specifications of 10-pin and 16-pin products
		p.2	Modification of description in 1.1 Features
		p.6	Modification of figure in 1.3.4 24-pin products
		p.11	Modification of figure in 1.5.3 20-pin products
		p.12	Modification of figure in 1.5.4 24-pin, 25-pin products

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